

L Number	Hits	Search Text	DB	Time stamp
1	210	john near2 lang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 11:36
2	1	(john near2 lang.in.) and (dimethyl near sulfoxide or dmsol or dimethylsulfoxide or dimethylsulfoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 11:37
-	438	(photoresist or resist or mask\$4) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:19
-	46	(photoresist or resist or mask\$4) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:48
-	1	(photoresist or resist or mask\$4) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same etch\$4 same (grad\$3 or hplc)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:37
-	9	(photoresist or resist or mask\$4) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same (grad\$3 or hplc)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:38
-	3776	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same (HPLC or liquid adj chromatography or high adj pressure near5 grade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:19
-	359	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (HPLC or liquid adj chromatography or high adj pressure near5 grade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:50
-	339	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (HPLC or pressure near2 liquid adj chromatography or high adj pressure near5 grade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:52
-	339	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (HPLC or pressure near2 liquid adj chromatography)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:52
-	1	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (HPLC or pressure near2 liquid adj chromatography) same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 15:54
-	1	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (HPLC or pressure near2 liquid adj chromatography) same (photoresist or resist or mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 16:08
-	2	5399202.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 16:18
-	2	5633175.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/28 16:18

-	196	hard near2 mask near10 (sio2 or "sio.sub.2" or silicon adj dioxide or silicon adj oxide) same (photoresist or resist) same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:19
-	19	hard near2 mask near10 (sio2 or "sio.sub.2" or silicon adj dioxide or silicon adj oxide) same (photoresist or resist) same dielectric same (ash\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:19
-	8851	low near2 dielectric near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:01
-	359	low near2 dielectric near2 (layer or film) same hard near2 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:01
-	359	low near2 dielectric near2 (layer or film) same hard near2 mask same (mask\$5 or photo\$1resist\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:01
-	32	low near2 dielectric near2 (layer or film) same hard near2 mask same (photo\$1resist\$5) same (strip\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:04
-	31	low near2 dielectric near2 (layer or film) same hard near2 mask same (photo\$1resist\$5) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:04
-	143	low near2 dielectric near2 (layer or film) same hard near2 mask same (photo\$1resist\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:36
-	0	low near2 dielectric near2 (layer or film) same hard near2 mask same (photo\$1resist\$5) and 6054379.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 16:42
-	40	low near2 dielectric near2 (layer or film) same (sio2 or "sio.sub.2" or silicon adj oxide or silicon adj dioxide or silicon adj nitride or sin) near5 mask same (photo\$1resist\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 17:28
-	66	((imd or inter\$1metal near2 dielectric) same (sio2 or "sio.sub.2" or silicon adj oxide or silicon adj dioxide or silicon adj nitride or sin or hard) near5 mask same (photo\$1resist\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 10:35
-	2	5959361.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 10:33
-	334	((imd or inter\$1metal near2 dielectric or low near2 (dielectric or k)) same (sio2 or "sio.sub.2" or silicon adj oxide or silicon adj dioxide or silicon adj nitride or sin or hard) near5 mask same (photo\$1resist\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 10:36
-	15	((imd or inter\$1metal near2 dielectric or low near2 (dielectric or k)) same (sio2 or "sio.sub.2" or silicon adj oxide or silicon adj dioxide or silicon adj nitride or sin or hard) near5 mask same (photo\$1resist\$5)) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 10:56

-	2003	teflon near5 dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/15 10:56
-	475	teflon near5 dielectric near2 constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/15 10:58
-	23	teflon near5 dielectric near2 constant near10 organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/15 10:56
-	303	teflon near5 dielectric near2 constant and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/15 10:58
-	6149	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same (HPLC or liquid adj chromatography or high adj pressure near5 grade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:19
-	90	(photoresist or resist or mask\$4) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:20
-	80	(photoresist or resist) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:30
-	0	(photoresist or resist) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5) near10 selectiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:21
-	8	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5) near10 selectiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:22
-	0	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (photoresist or resist) near10 selectiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:22
-	1	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near20 (photoresist or resist) near20 selectiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:23
-	3	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same (photoresist or resist) same ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:26
-	197	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:26
-	8	(remov\$5 or strip\$) near20 (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:27

-	74	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near20 (photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:17
-	1	((photoresist or resist) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5)) same ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:30
-	13	((photoresist or resist) same (dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near10 (remov\$5 or strip\$5)) and ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:34
-	3843	(strip\$5 or remov\$5) near10 (photoresist or resist) and ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:35
-	382	(strip\$5 or remov\$5) near10 (photoresist or resist) and ultrasonic near5 bath	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:35
-	1	(strip\$5 or remov\$5) near10 (photoresist or resist) and ultrasonic near5 bath near10 advantag\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:35
-	0	(strip\$5 or remov\$5) near10 (photoresist or resist) same ultrasonic near5 bath near10 advantag\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:36
-	146	(strip\$5 or remov\$5) near10 (photoresist or resist) same ultrasonic near5 bath	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:36
-	85	(strip\$5 or remov\$5) near10 (photoresist or resist) same ultrasonic near5 bath and @py<1999	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:37
-	3	"act-690" near10 ashland	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:38
-	4	"act-690" near10 (ashland or asland)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 14:38
-	4	"act-690" near10 (ashland or asland or stripper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:12
-	1	"act-690" and liu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:12
-	7	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") near20 (photoresist) near20 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:19

-	37	(dimethylsulfoxide or dimethylsulfoxide or dmsol or "c.sub.2h.sub.6os") same (resist photoresist) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:24
-	53	act near "690"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:26
-	7	act near "690" near10 (asland or ashland)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:25
-	1	act near "690" near15 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:30
-	2090	(photo near resist or resist or photoresist) same ultrasonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:31
-	1	(photo near resist or resist or photoresist) same ultrasonic adj bath same (dimethyl sulfoxide or dmsol or act near "690")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:31
-	0	(photo near resist or resist or photoresist) same ultrasonic adj bath near5 advantag\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:32
-	1	(photo near resist or resist or photoresist) same ultrasonic adj bath near5 improv\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:32
-	144	(photo near resist or resist or photoresist) same ultrasonic adj bath	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:37
-	42374	noe near10 strip\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:34
-	51	noe near5 advanced near10 strip\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:35
-	51	"noe" near5 advanced near10 strip\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:35
-	0	"noe"! near5 advanced near10 strip\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:35
-	6	noe! near10 strip\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/16 15:36

-	2	(photo near resist or resist or photoresist) same ultrasonic adj bath near5 technique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 15:40
-	3	(photo near resist or resist or photoresist) same ultrasonic adj bath same act	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:10
-	1	(photo near resist or resist or photoresist) same ultrasonic adj bath near10 prefer\$7	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:10
-	1	(photo near resist or resist or photoresist) same ultrasonic adj bath near10 prefer\$5	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:10
-	2	(photo near resist or resist or photoresist) same ultrasonic adj bath near10 (improv\$4 or advantag\$5 or prefer\$5)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:11
-	63	(photo near resist or resist or photoresist) same ultrasonic near10 (improv\$4 or advantag\$5 or prefer\$5)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:11